

## LCE P-Channel Enhancement Mode Power MOSFET

**Description**

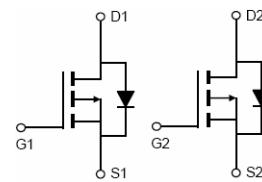
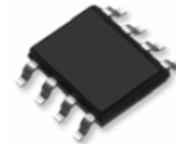
The LCE4801 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

**General Features**

- $V_{DS} = -30V, I_D = -5A$
- $R_{DS(ON)} < 80m\Omega @ V_{GS}=-2.5V$
- $R_{DS(ON)} < 57m\Omega @ V_{GS}=-4.5V$
- $R_{DS(ON)} < 48m\Omega @ V_{GS}=-10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

**Application**

- PWM applications
- Load switch
- Power management

**Schematic diagram****Marking and Pin Assignment****SOP-8 top view****Package Marking And Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4801	LCE4801	SOP-8	Ø330mm	12mm	4000 units

**Absolute Maximum Ratings (TA=25°C unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	-5	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	-28	A
Maximum Power Dissipation	$P_D$	2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	62.5	°C/W
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**Electrical Characteristics (TA=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	$\mu A$



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Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <small>(Note 3)</small>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.7	-1	-1.3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-5A$	-	40	48	$m\Omega$
		$V_{GS}=-4.5V, I_D=-4A$	-	45	57	$m\Omega$
		$V_{GS}=-2.5V, I_D=-3A$		60	80	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-5A$	-	10	-	S
<b>Dynamic Characteristics</b> <small>(Note 4)</small>						
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V, F=1.0MHz$	-	880	-	PF
Output Capacitance	$C_{oss}$		-	105	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	65	-	PF
<b>Switching Characteristics</b> <small>(Note 4)</small>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-5A$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	7	-	nS
Turn-on Rise Time	$t_r$		-	3	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	$t_f$		-	12	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-15V, I_D=-5A, V_{GS}=-4.5V$	-	8.5	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.8	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.7	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <small>(Note 3)</small>	$V_{SD}$	$V_{GS}=0V, I_S=-5A$	-	-	-1.2	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production



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### Typical Electrical and Thermal Characteristics

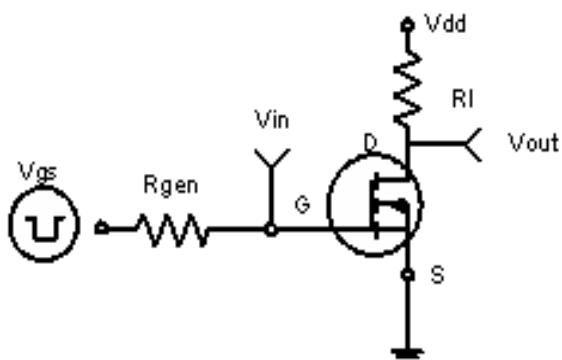


Figure 1:Switching Test Circuit

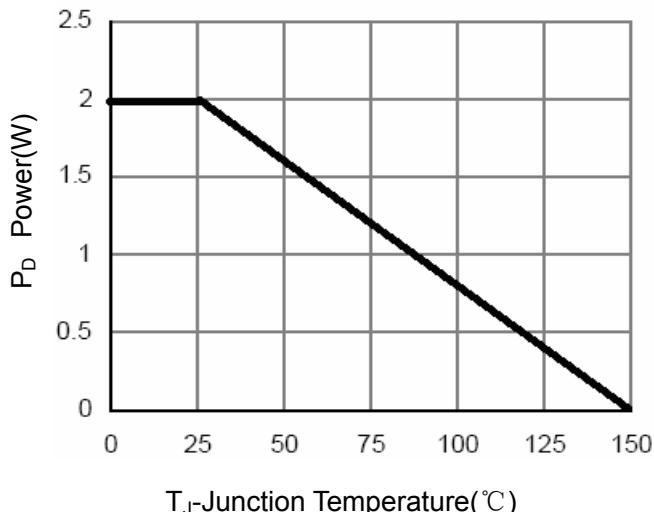


Figure 3 Power Dissipation

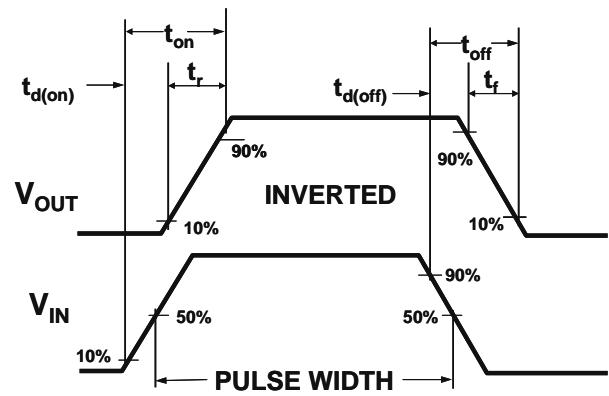


Figure 2:Switching Waveforms

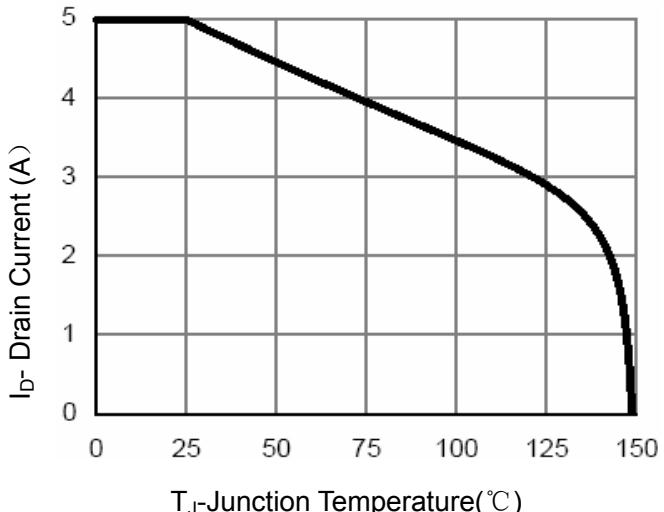


Figure 4 Drain Current

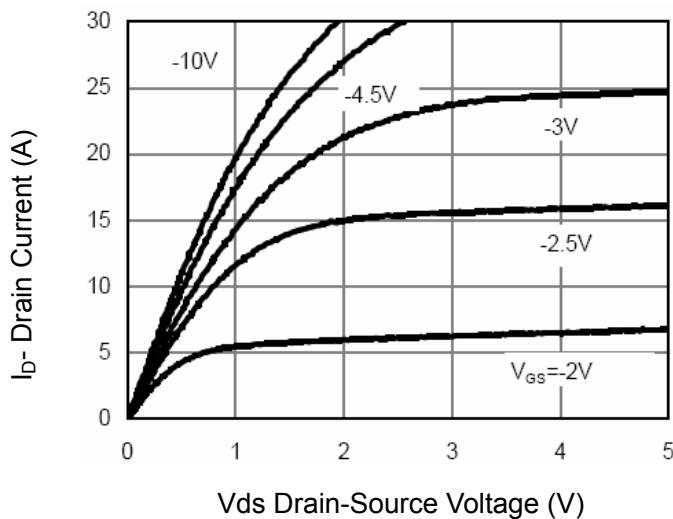


Figure 5 Output Characteristics

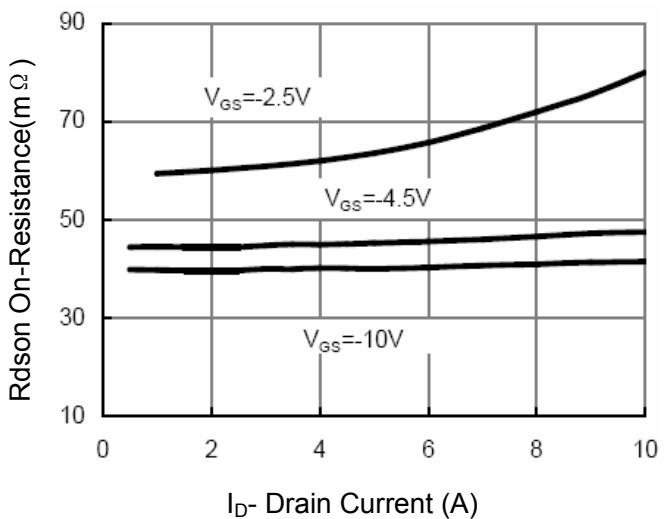


Figure 6 Drain-Source On-Resistance



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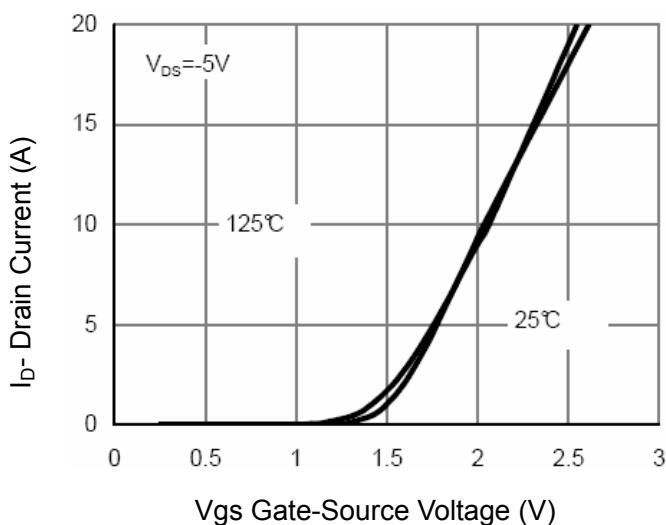


Figure 7 Transfer Characteristics

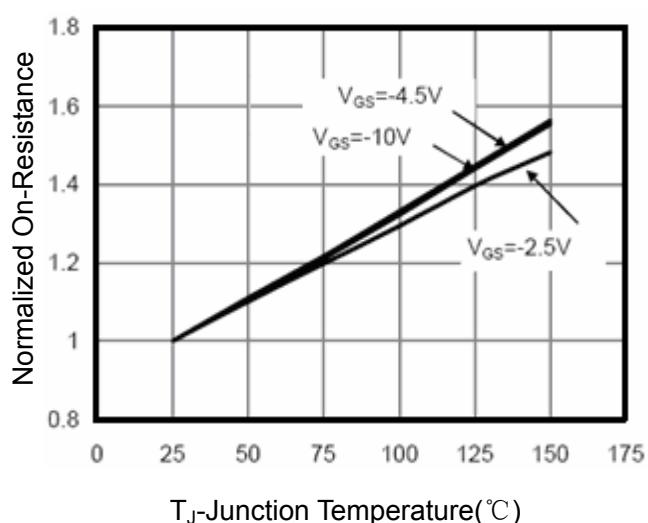


Figure 8 Drain-Source On-Resistance

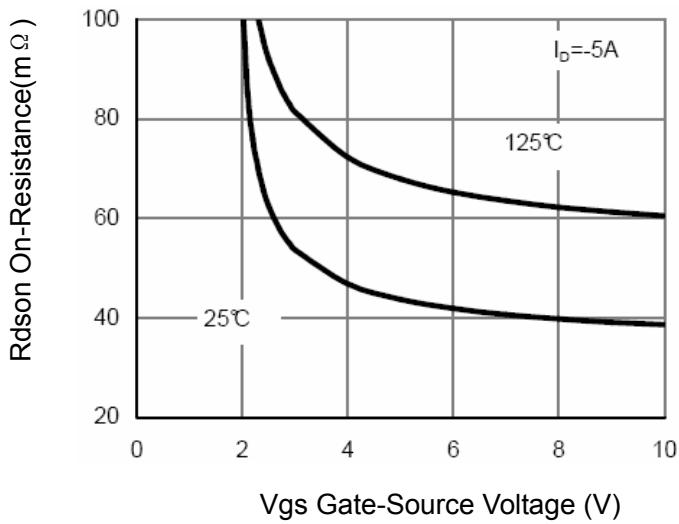


Figure 9  $R_{DSON}$  vs  $V_{GS}$

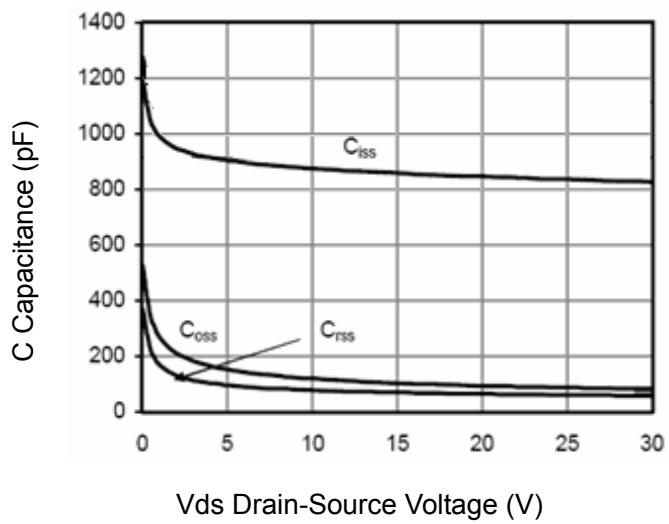


Figure 10 Capacitance vs  $V_{DS}$

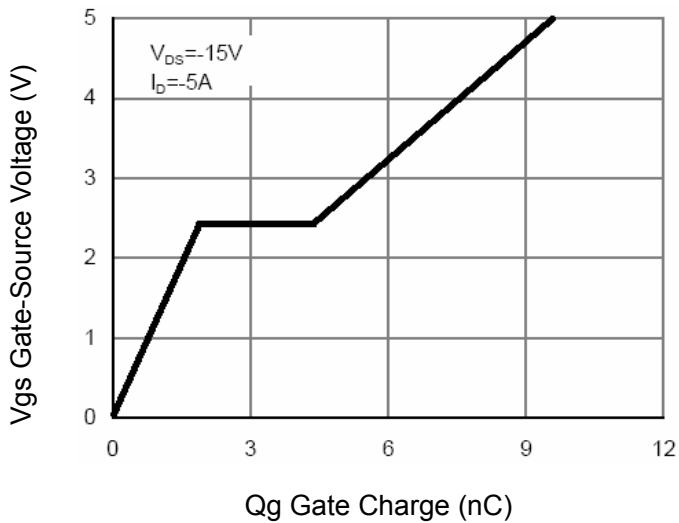


Figure 11 Gate Charge

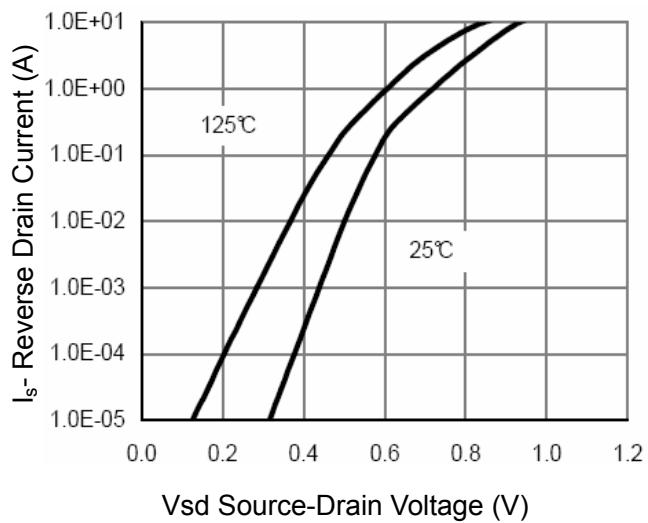
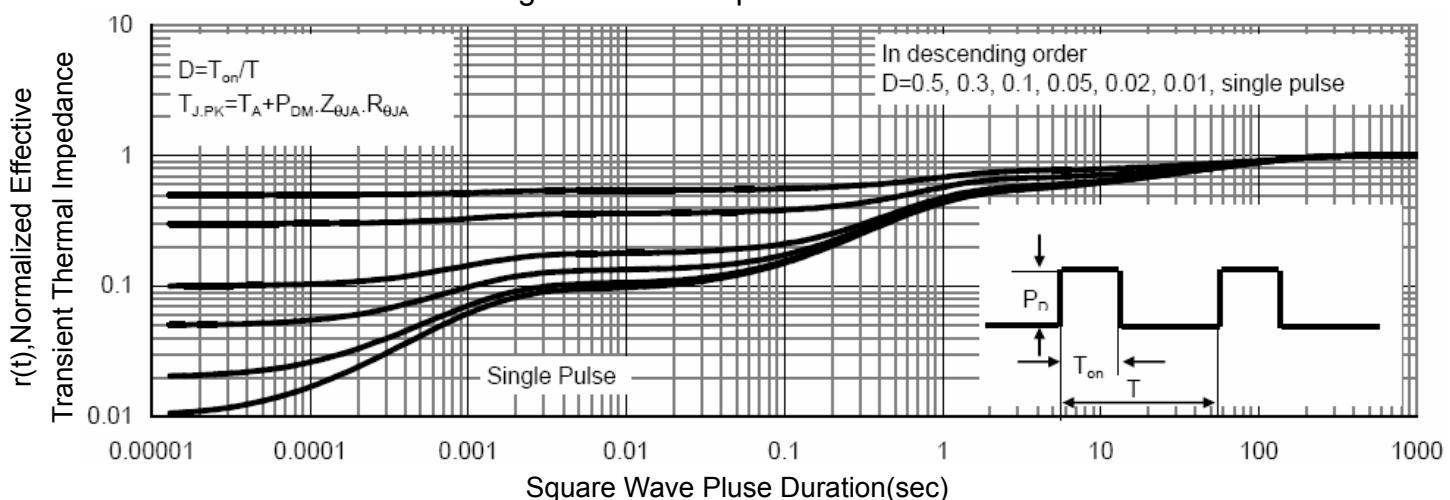
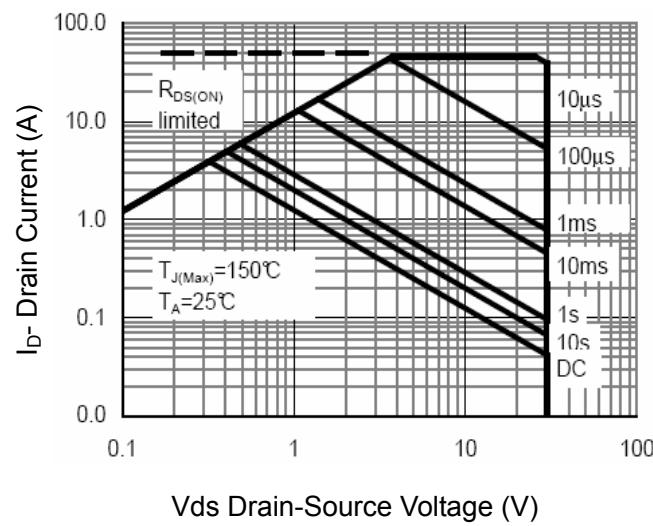
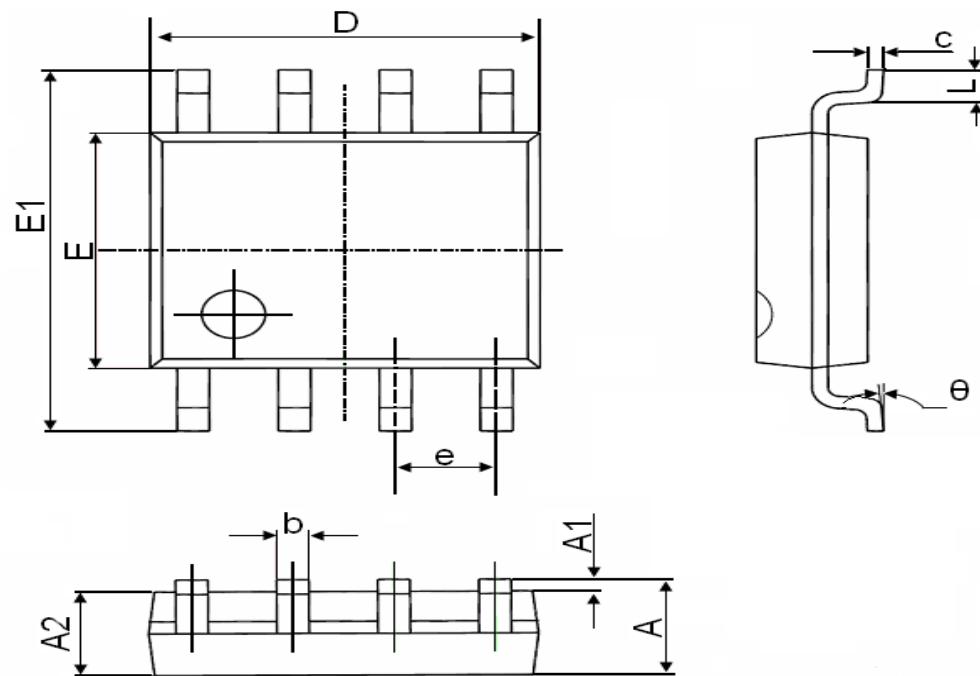


Figure 12 Source-Drain Diode Forward



**SOP-8 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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